## Dual Surface Mount Switching Diode KAV70W (BAV70W)

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance


Absolute Maximum Ratings $\mathrm{Ta}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Rating | Unit |
| :---: | :---: | :---: | :---: |
| Non-Repetitive Peak Reverse Voltage | VRM | 100 | V |
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | VRRM <br> VRWM <br> VR | 75 | V |
| RMS Reverse Voltage | V R(RMS) | 50 | V |
| Average Rectified Output Current | Io | 150 | mA |
| Forward Continuous Current | IFM | 300 | mA |
| Non-Repetitive Peak Forward Surge Current @t $=1.0 \mu \mathrm{~s}$ <br> @ $t=1.0 s$ | IFSM | $\begin{aligned} & \hline 2.0 \\ & 1.0 \end{aligned}$ | A |
| Power Dissipation | Pd | 200 | mW |
| Thermal Resistance Junction to Ambient Air | R ${ }^{\text {JA }}$ | 625 | K/W |
| Operating and Storage Temperature Range | T,TstG | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

Electrical Characteristics $\mathrm{Ta}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Reverse Breakdown Voltage | V (BR)R | $\mathrm{IF}=10 \mu \mathrm{~A}$ | 75 |  |  | V |
| Forward Voltage | VF | $\begin{aligned} & \mathrm{IF}=1.0 \mathrm{~mA} \\ & \mathrm{IF}=10 \mathrm{~mA} \\ & \mathrm{IF}=50 \mathrm{~mA} \\ & \mathrm{IF}=150 \mathrm{~mA} \end{aligned}$ |  |  | $\begin{array}{\|c\|} \hline 0.715 \\ 0.855 \\ 1.0 \\ 1.25 \end{array}$ | V |
| Peak Reverse Current | IRM | $\begin{aligned} & V_{R}=75 \mathrm{~V} \\ & V_{R}=75 \mathrm{~V}, T_{j}=150^{\circ} \mathrm{C} \\ & V_{R}=25 \mathrm{~V}, T_{j}=150^{\circ} \mathrm{C} \\ & V_{R}=20 \mathrm{~V} \end{aligned}$ |  |  | $\begin{aligned} & 2.5 \\ & 50 \\ & 30 \\ & 25 \end{aligned}$ | $\begin{aligned} & \mu \mathrm{A} \\ & \mu \mathrm{~A} \\ & \mu \mathrm{~A} \\ & \mathrm{nA} \end{aligned}$ |
| Junction Capacitance | $\mathrm{C}_{\mathrm{j}}$ | $\mathrm{V}_{\mathrm{R}}=0, \mathrm{f}=1.0 \mathrm{MHz}$ |  |  | 2 | pF |
| Reverse Recovery Time | trr | $\mathrm{IF}=\mathrm{IR}=10 \mathrm{~mA}, \mathrm{Irr}=0.1 \mathrm{XIR}, \mathrm{RL}=100 \Omega$ |  |  | 4 | ns |

Marking

| Marking | A4* |
| :---: | :---: |

## KAV70W (BAV70W)

■ Typical Characterisitics


Device mounted on an FR4 printed-circuit board.
Fig. 1 Maximum permissible continuous forward current as a function of ambient temperature.


Fig. 3 Reverse current as a function of junction temperature.

(1) $\mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$; typical values.
(2) $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; typical values.
(3) $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; maximum values.

Fig. 2 Forward current as a function of forward voltage.

$\mathrm{f}=1 \mathrm{MHz} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$.

Fig. 4 Diode capacitance as a function of reverse voltage; typical values.

